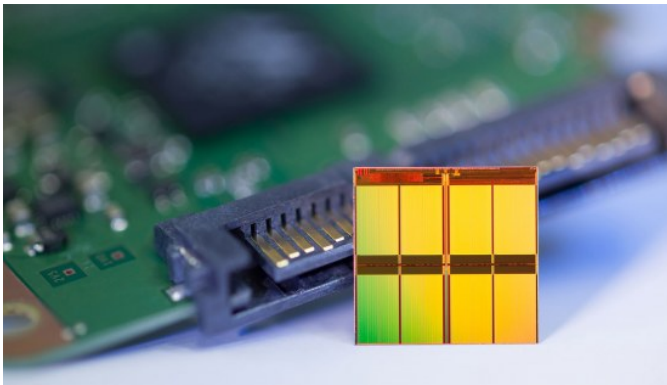


Micron Unveils 16nm NAND Flash

Written by Marco Attard
18 July 2013

Micron Technology starts sampling 128Gb multi-level cell (MLC) NAND flash memory made using 16nm process technology, an industry first allowing for increasingly smaller memory devices.



The 16nm technology is also "the most advanced processing node for any sampling semiconductor device" the company claims.

"Our customers continually ask for higher capacities in smaller form factors, and this next-generation process node allows Micron to lead the market in meeting those demands," Micron says.

The 128Gb MLC NAND flash memory devices are designed for SSDs, removable storage (USB drives and flash cards), mobile devices, ultrathin devices and data centre storage. Offering both greater storage per square millimeter and lower costs, Micron says the technology creates nearly 6TB of storage on a single wafer.

Full 16nm flash memory production kicks off in Q4 2013, and Micron will also launch an SSD line based on the technology sometime during 2014.

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